UNISONIC TECHNOLOGIES CO., LTD

UGP7N60

Preliminary

Insulated Gate Bipolar Transistor

600V, SMPS N-CHANNEL IGBT

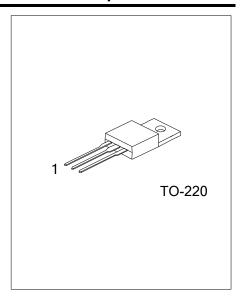
■ DESCRIPTION

The UT C **UGP7N60** is an N-chann el IGBT . it uses U TC's advanced tec hnology to provide custo mers with h igh i nput impedance, high switching speed and low conduction loss, etc.

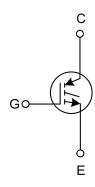
The UTC **UGP7N60** is suitable for high voltages witching, high frequency switch mode power supplies.

■ FEATURES

- * High switching speed
- * High input impedance
- * Low conduction loss

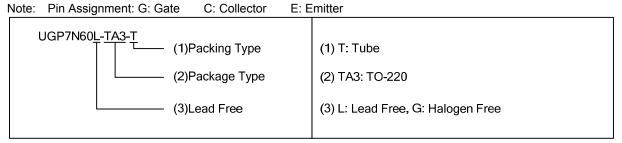


■ SYMBOL



■ ORDERING INFORMATION

| Ordering Number | | Dookogo | Pin Assignment | | | Dooking | |
|-----------------|----------------|---------|----------------|---|---|---------|--|
| Lead Free | Halogen Free | Package | 1 | 2 | 3 | Packing | |
| UGP7N60L-TA3-T | UGP7N60G-TA3-T | TO-220 | G | С | E | Tube | |



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■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

| PARAMETER SYMBOL | | | RATINGS | UNIT | |
|--|-----------------------------|---------------------|----------------------|------|--|
| Collector-Emitter Voltage | | V _{CES} 60 | 0 | V | |
| Continuous Collector Current | T _C =25°C | | 34 A | | |
| | T _C =110°C 14 | I _C | | Α | |
| Collector Current Pulsed (Note 2) | | I _{CM} 56 | | Α | |
| Gate to Emitter Voltage Continuous | | V _{GES} ±2 | V _{GES} ±20 | | |
| Gate to Emitter Voltage Pulsed | | V _{GEM} ±3 | V _{GEM} ±30 | | |
| Switching Safe Operating Area at T _J =150°C | | SSOA | 35 (at 600V) | Α | |
| Single Pulse Avalanche Energ | y at T _C =25°C E | AS | AS 25 (at 7A) | | |
| Power Dissipation Total at T _C =25°C P | | _D 125 | | W | |
| Power Dissipation Derating T _C >25°C | | | 1.0 | W/°C | |
| Junction Temperature | ction Temperature | | +150 | °C | |
| Storage Temperature Range | rage Temperature Range | | 5~ +150 | °C | |

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

Absolute maximum ratings are those values beyond which the device could be permanently damaged.

■ THERMAL CHARACTERISTICS

| PARAMETER SYMBOL | | RATINGS | UNIT |
|------------------|---------------------|---------|------|
| Junction to Case | θ _{JC} 1.0 | | °C/W |

■ **ELECTRICAL CHARACTERISTICS** (T_J=25°C, unless otherwise specified)

| PARAMETER SYMBOL | | TEST CONDITIONS | | MIN | TYP | MAX | UNIT |
|--|---|---|---|-----------------|-----|------|-----------------------|
| Collector-Emitter Breakdown Voltage | BV _{CES} | I _C =250μA, V _{GE} =0V 600 | | | | | V |
| Emitter to Collector Breakdown Voltage | BV _{ECS} | I _C =10mA, V _{GE} =0V 20 | | | | | V |
| Oallantan Freittan Lankana Ourmant | I _{CES} | V _{CE} =600V | T _J =25°C | | | 250 | μΑ |
| Collector-Emitter Leakage Current | | | T _J =125°C | | | 2 | mA |
| Collector-Emitter Saturation Voltage | V _{CE(SAT)} | I _C =7A, V _{GE} =15V | T _J =25°C | | 1.3 | 2.7 | V |
| | | | T _J =125°C | | 1 | 2.2 | V |
| Gate to Emitter Threshold Voltage | $V_{GE(TH)}$ | I _C =250μA | | 4.5 | 5.9 | 7.2 | V |
| Gate to Emitter Leakage Current | I _{GES} | V _{GE} =±20V | | | | ±250 | nA |
| Switching SOA | SSOA | $T_J=150^{\circ}C, R_G=25\Omega, V_{GE}=15V$ | | 35 | | | Α |
| | | • | | | | | |
| Pulsed Avalanche Energy | E _{AS} | I _{CE} =7A, L=500μH | | 25 | | | mJ |
| Gate to Emitter Plateau Voltage | V_{GEP} | I _C =7A, V _{CE} =80V | | 10 | | | V |
| On State Cate Charge | $Q_{g(ON)}$ | I _C =7A, V _{CE} =300V | V _{GE} =15V | | 37 | 45 | nC |
| On-State Gate Charge | | | V _{GE} =20V | | 48 | 60 | nC |
| Current Turn-On Delay Time | t _{dON)I} | IGBT and Diode at T_J =25°C, I_{CE} =7A, V_{GE} =13.5V, R_G =50 Ω , R_L =1 Ω , Test Circuit (Note 1) | | 400 |) | | ns |
| Current Rise Time | t _{rl} | | | | 2.6 | | μs |
| Current Turn-Off Delay Time | t _{dOFF)I} | | | | 300 | | ns |
| Current Fall Time | t _{fl} | | | 2 | | | μs |
| Switching SOA Pulsed Avalanche Energy Gate to Emitter Plateau Voltage On-State Gate Charge Current Turn-On Delay Time Current Rise Time Current Turn-Off Delay Time | $SSOA$ E_{AS} V_{GEP} $Q_{g(ON)}$ $t_{dON)l}$ t_{rl} $t_{dOFF)l}$ | $\begin{split} &T_{J}{=}150^{\circ}\text{C}, \ R_{G}{=}25\Omega, \\ &L{=}100\mu\text{H}, \ V_{GE}{=}600\text{V} \\ &I_{CE}{=}7\text{A}, \ L{=}500\mu\text{H} \\ &I_{C}{=}7\text{A}, \ V_{CE}{=}80\text{V} \\ &I_{C}{=}7\text{A}, \ V_{CE}{=}300\text{V} \\ &-\text{IGBT and Diode at T} \\ &I_{CE}{=}7\text{A}, \ V_{GE}{=}13.5\text{V}, \end{split}$ | V_{GE} =15 V_{GE} =20 V_{J} =25° C , R_{G} =50 Ω , | 25 10 400 | 48 | 45 | A MC nC nC ns µs |

Note: 1.Pulse Test: Pulse width ≤ 50 µs.

^{2.} Pulse width limited by maximum junction temperature.

■ TEST CIRCUIT AND WAVEFORMS

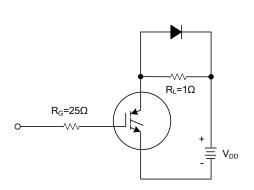


Fig 1. INDUCTIVE SWITCHING TEST CIRCUIT

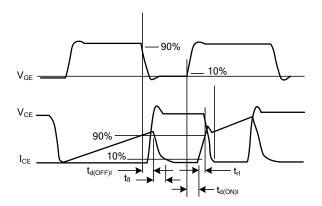


Fig 2. SWITCHING TEST WAVEFORMS

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